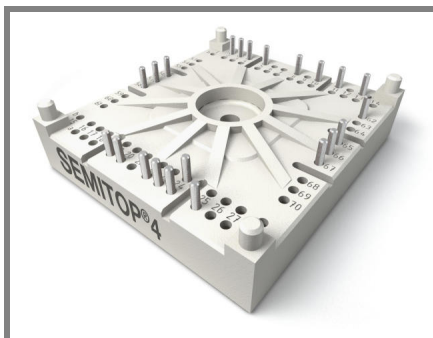


SK200GD066T



SEMITOP® 4

IGBT Module

SK200GD066T

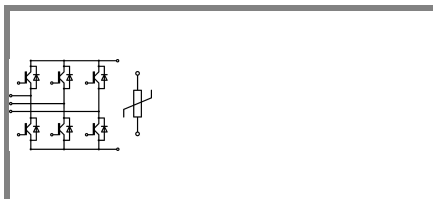
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

- Inverter up to 42 kVA
- Typ. motor power 18,5 kW

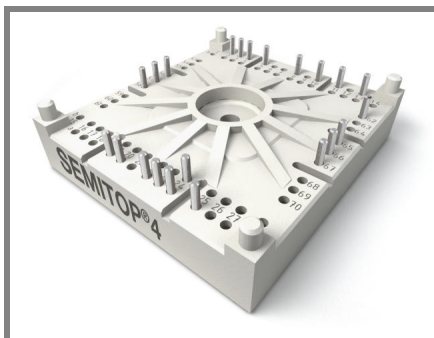


GD-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	174 A
		$T_s = 70\text{ °C}$	131 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	400	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	6	μs
Inverse Diode			
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	99 A
		$T_s = 70\text{ °C}$	79 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	120	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +150	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3,2\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,01	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		1200	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	0,6	1	V
		$T_j = 150\text{ °C}$	0,7	0,8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	2,75	4	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	4,25	5,5	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 200\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,9	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,7	2,15	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	12,2		nF
C_{oes}			0,76		nF
C_{res}			0,36		nF
$t_{d(on)}$	$R_{Gon} = 16\ \Omega$ $di/dt = 1720\text{ A}/\mu\text{s}$	$V_{CC} = 300\text{ V}$ $I_C = 200\text{ A}$	144		ns
t_r			128		ns
E_{on}			13,9		mJ
$t_{d(off)}$	$R_{Goff} = 16\ \Omega$ $di/dt = 2575\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	1040		ns
			91		ns
E_{off}			12		mJ
$R_{th(j-s)}$	per IGBT		0,45		K/W

SK200GD066T



SEMITOP® 4

IGBT Module

SK200GD066T

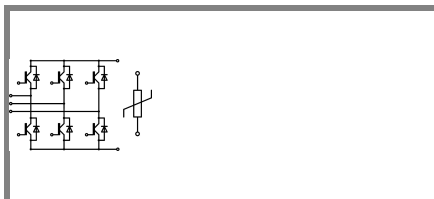
Preliminary Data

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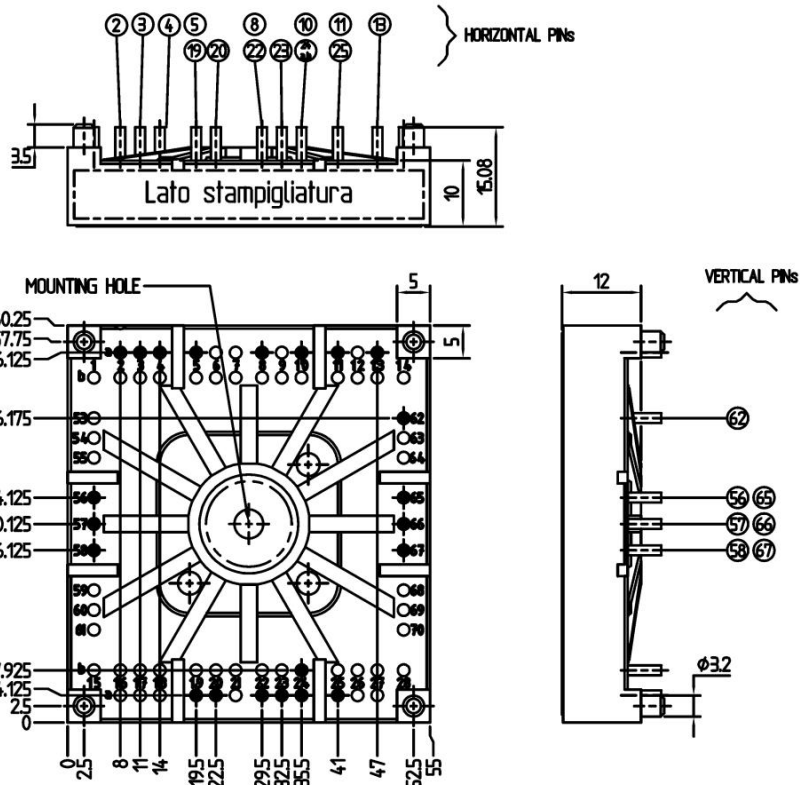
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Characteristics

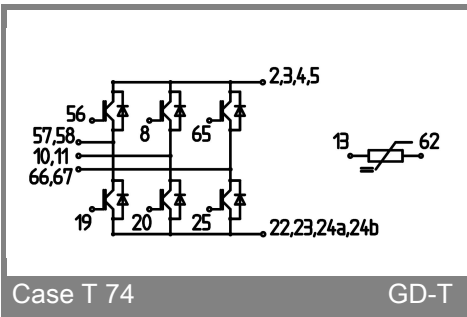
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,3		V
		$T_j = 150 \text{ }^\circ\text{C}_{chiplev.}$	1,3		V
V_{F0}		$T_j = 25 \text{ }^\circ\text{C}$	0,95		V
		$T_j = 150 \text{ }^\circ\text{C}$	0,85		V
r_F		$T_j = 25 \text{ }^\circ\text{C}$	3,5		mΩ
		$T_j = 150 \text{ }^\circ\text{C}$	4,5		mΩ
I_{RRM}	$I_F = 200 \text{ A}$		120		A
Q_{rr}	$di/dt = 1720 \text{ A}/\mu\text{s}$		12		μC
E_{rr}	$V_{CC} = 300\text{V}$		3,4		mJ
$R_{th(j-s)D}$	per diode		0,8		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C} (R_{25} = 5\text{k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T